



#### IPP80N06S207AKSA4 Information



For Reference Only

Part Number IPP80N06S207AKSA4
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 55V 80A TO220-3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# IPP80N06S207AKSA4 Specifications

Manufacturer Part Number         IPP80N06S207AKSA4           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         55V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 180µA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3400pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         250W (Tc)           Rds On (Max) @ Id, Vgs         6.6 mOhm @ 68A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3-1           Package / Case         TO-220-3		
Category         Discrete Semiconductor Products           Package         TO-220-3           Series         OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         55V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 180µA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3400pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         250W (Tc)           Rds On (Max) @ Id, Vgs         6.6 mOhm @ 68A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3-1           Package / Case         TO-220-3	Manufacturer Part Number	IPP80N06S207AKSA4
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FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         55V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 180μA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3400pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         250W (Tc)           Rds On (Max) @ Id, Vgs         6.6 mOhm @ 68A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3-1           Package / Case         TO-220-3	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 180μA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package PG-TO220-3-1 Package / Case  MOSFET (Metal Oxide)  55V 660 MCS 660 (Tc) 80A (Tc) 8	Series	OptiMOS?
Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 180μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3400pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs6.6 mOhm @ 68A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C       80A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       4V @ 180μA         Gate Charge (Qg) (Max) @ Vgs       110nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       3400pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       250W (Tc)         Rds On (Max) @ Id, Vgs       6.6 mOhm @ 68A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PG-TO220-3-1         Package / Case       TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 180μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3400pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs6.6 mOhm @ 68A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	55V
Vgs(th) (Max) @ Id       4V @ 180μA         Gate Charge (Qg) (Max) @ Vgs       110nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       3400pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       250W (Tc)         Rds On (Max) @ Id, Vgs       6.6 mOhm @ 68A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PG-TO220-3-1         Package / Case       TO-220-3	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs       110nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       3400pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       250W (Tc)         Rds On (Max) @ Id, Vgs       6.6 mOhm @ 68A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PG-TO220-3-1         Package / Case       TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  6.6 mOhm @ 68A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3-1  Package / Case  TO-220-3	Vgs(th) (Max) @ Id	4V @ 180μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs6.6 mOhm @ 68A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	110nC @ 10V
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	3400pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  6.6 mOhm @ 68A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3-1  Package / Case  TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs6.6 mOhm @ 68A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3-1  Package / Case  TO-220-3	Power Dissipation (Max)	250W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	6.6 mOhm @ 68A, 10V
Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	PG-TO220-3-1
Report errors?	Package / Case	TO-220-3
		Report errors?

#### IPP80N06S207AKSA4 Guarantees



#### **Ouality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### IPP80N06S207AKSA4 Payment Methods



















# IPP80N06S207AKSA4 Shipping Methods













If you have any question about IPP80N06S207AKSA4, please do not hesitate to contact us!

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